

INTERNATIONAL INDIAN SCHOOL BURAIDAH

CLASS:XII SUBJECT: PHYSICS

LESSON : SEMICONDUCTOR ELECTRONICS

1. At a certain temperature in an intrinsic semiconductor, the electrons and holes concentration is $1.5 \times 10^{-16} \text{ m}^{-3}$. When it is doped with a trivalent dopant, hole concentration increases to $4.5 \times 10^{22} \text{ m}^{-3}$. In the doped semiconductor, the concentration of electrons (n_e) will be (CBSE 2023)
 - (a) $3 \times 10^6 \text{ m}^{-3}$
 - (b) $5 \times 10^7 \text{ m}^{-3}$
 - (c) $5 \times 10^9 \text{ m}^{-3}$
 - (d) $6.75 \times 10^{38} \text{ m}^{-3}$
2. During the formation of a p-n junction (CBSE 2023)
 - (a) diffusion current keeps increasing
 - (b) drift current remains constant
 - (c) both the diffusion current and drift current remain constant.
 - (d) diffusion current remains almost constant but drift current increases till both currents-become equal
3. The formation of depletion region in a p-n junction diode is due to (CBSE 2023)
 - (a) movement of dopant atoms
 - (b) diffusion of the electrons and holes
 - (c) drift of electrons only
 - (d) drift of holes only
4. If a p-n junction diode is reverse biased.
 - (a) the potential barrier is lowered.
 - (b) the potential barrier remains unaffected.
 - (c) the potential barrier is raised
 - (d) the current is mainly due to majority charge carriers.
5. (1) (a) A germanium crystal is doped with antimony. With the help of energy-band diagram, explain how the conductivity of the doped crystal is affected.

6. Briefly explain the two processes involved in the formation of a p-n junction.
- (c) What will the effect of (I) forward biasing, and (II) reverse biasing be on the width of depletion layer in a p-n junction diode? (CBSE 2023)
7. Draw energy band diagram for an n- type and p-type semiconductor at $T > 0$ K. (CBSE 2023)
8. Explain the roles of diffusion current and drift current in the formation of the depletion layer in a p-n junction diode.
9. Name the device which converts an AC input signal into a DC output signal. Write the principle of working of the device.(CBSE 2022)
10. Explain the property of a p-n junction which makes it suitable for rectifying alternating voltages. Differentiate between a half-wave and a full-wave rectifier. (CBSE 2023)